



- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary



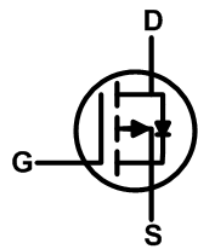
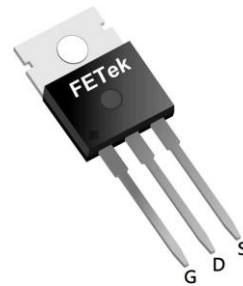
BVDSS	RDSON	ID
-100V	50mΩ	-35A

Description

The FKP0139 uses advanced trench MOSFET technology to provide excellent $R_{DS(ON)}$ and gate charge for use in a wide variety of other applications.

The FKP0139 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO220 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, V_{GS} @ -10V ¹	-35	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, V_{GS} @ -10V ¹	-23	A
I_{DM}	Pulsed Drain Current ²	-100	A
EAS	Single Pulse Avalanche Energy ³	345	mJ
I_{AS}	Avalanche Current	28	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	104	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.2	$^\circ C/W$

**Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-10A$	---	42	50	m Ω
		$V_{GS}=-4.5V, I_D=-8A$	---	46	55	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2	-1.8	-2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-100V, V_{GS}=0V, T_J=25^\circ C$	---	---	-50	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=-10V, I_D=-10A$	---	32	---	S
Q_g	Total Gate Charge	$V_{DS}=-80V, V_{GS}=-10V, I_D=-14A$	---	92	---	nC
Q_{gs}	Gate-Source Charge		---	17.5	---	
Q_{gd}	Gate-Drain Charge		---	14	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-50V, V_{GS}=-10V, R_G=3.3\Omega, I_D=-14A$	---	20.5	---	ns
T_r	Rise Time		---	32.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	123	---	
T_f	Fall Time		---	63.7	---	
C_{iss}	Input Capacitance	$V_{DS}=-25V, V_{GS}=0V, f=1MHz$	---	6516	---	pF
C_{oss}	Output Capacitance		---	223	---	
C_{rss}	Reverse Transfer Capacitance		---	125	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-35	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ C$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=-14A, di/dt=-100A/\mu s,$	---	31.2	---	nS
Q_{rr}	Reverse Recovery Charge	$T_J=25^\circ C$	---	31.97	---	nC

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating. The test condition is $V_{DD}=-25V, V_{GS}=-10V, L=0.88mH, I_{AS}=-28A$
4. The power dissipation is limited by 150 $^\circ C$ junction temperature
5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

Typical Characteristics

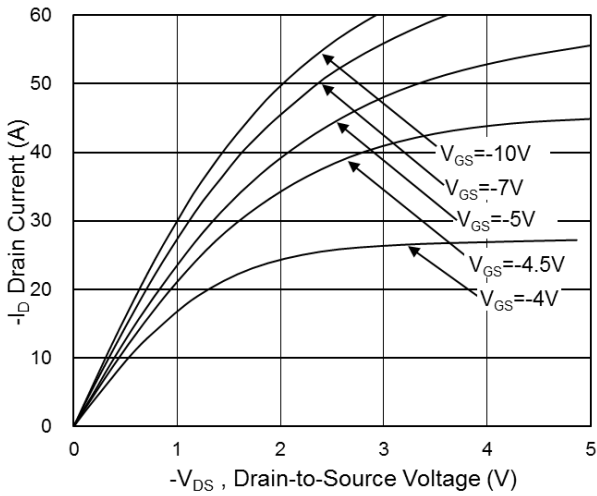


Fig.1 Typical Output Characteristics

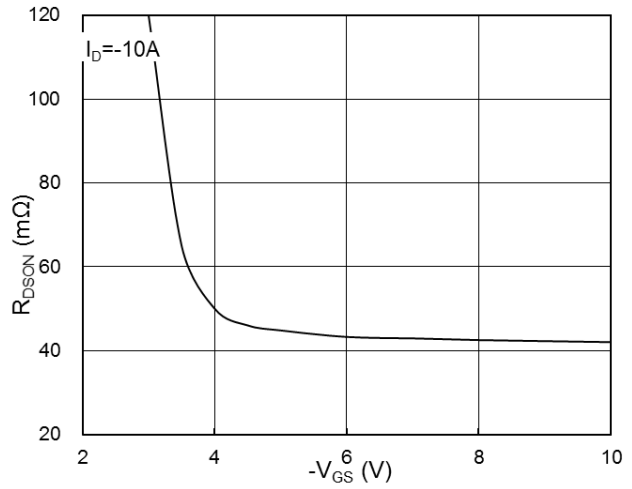


Fig.2 On-Resistance vs. G-S Voltage

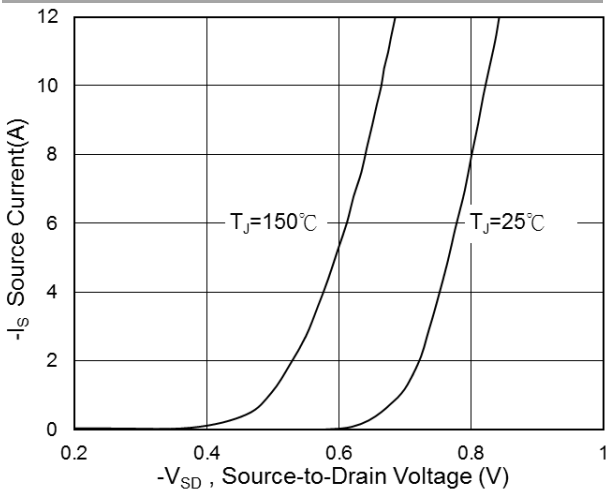


Fig.3 Typical S-D Diode Forward Voltage

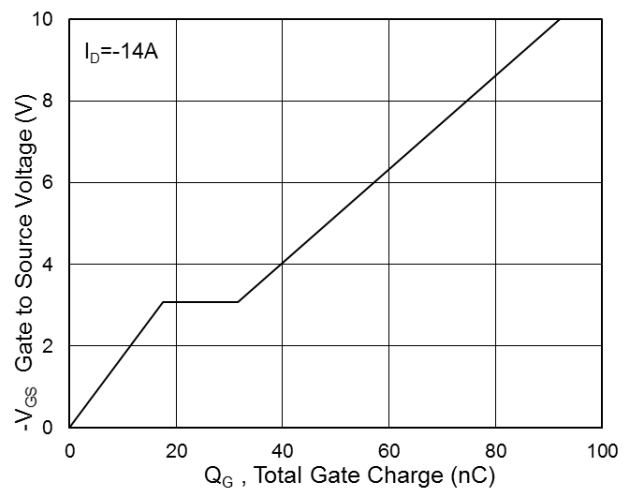


Fig.4 Gate-Charge Characteristics

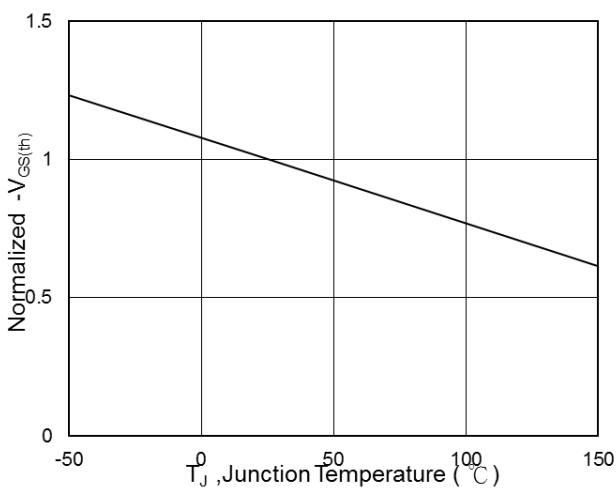


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

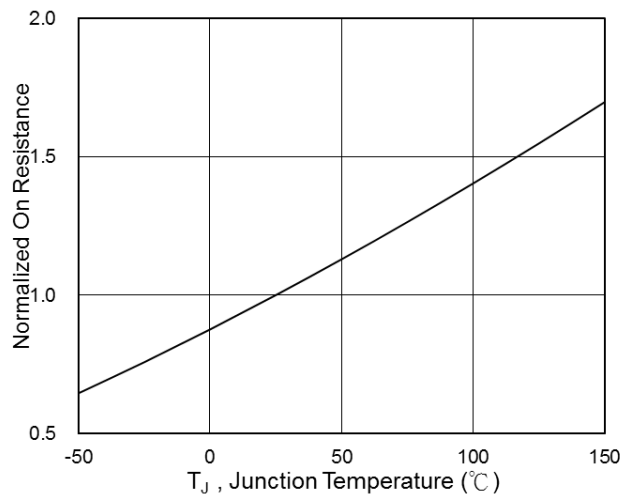


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

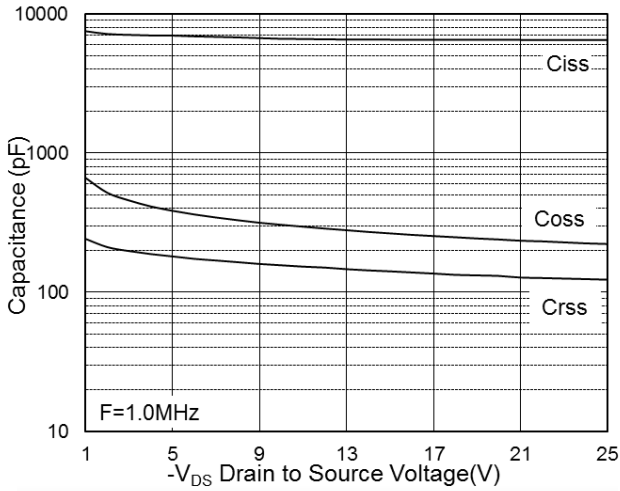


Fig.7 Capacitance

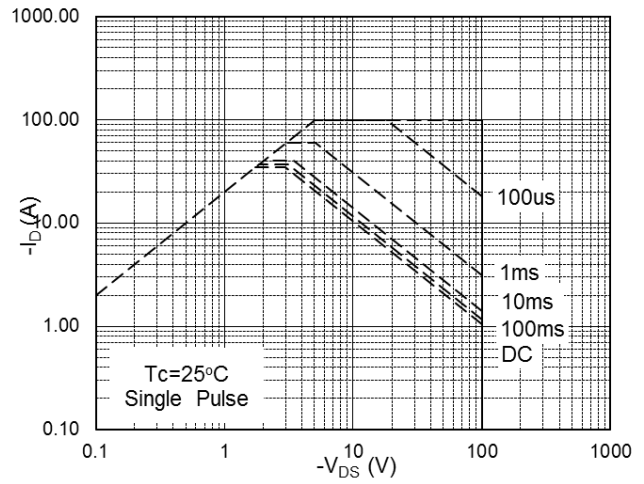


Fig.8 Safe Operating Area

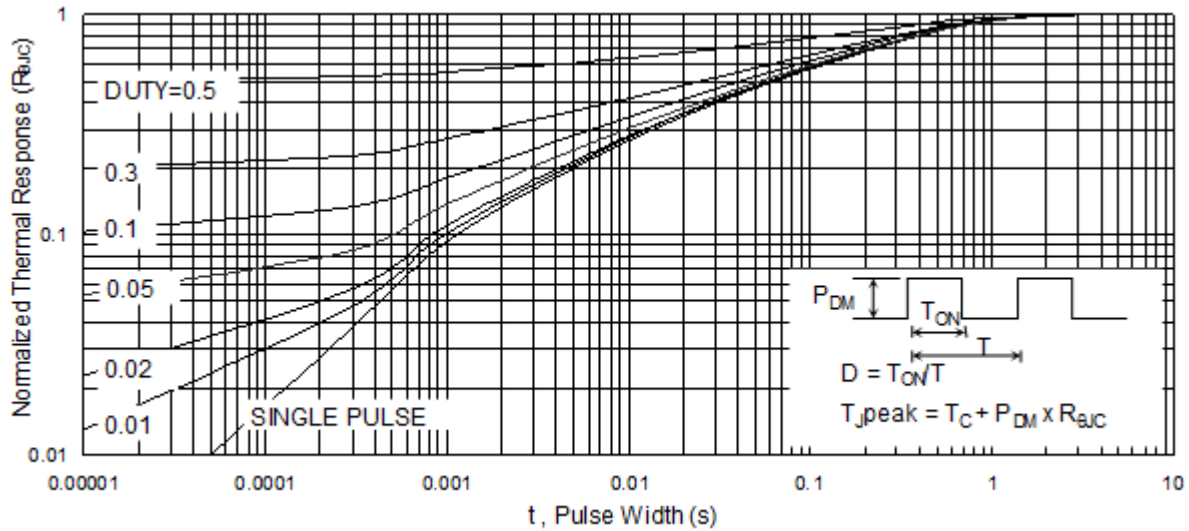


Fig.9 Normalized Maximum Transient Thermal Impedance

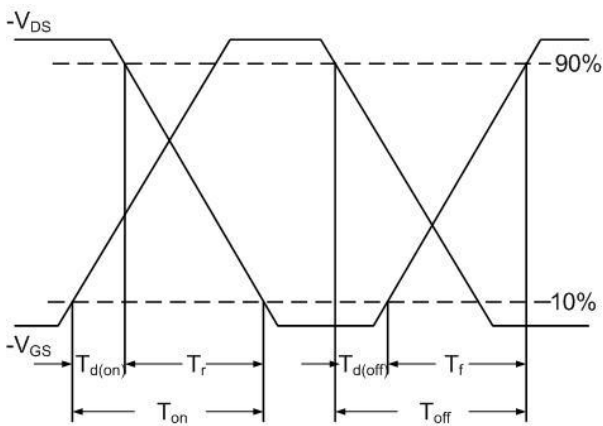


Fig.10 Switching Time Waveform

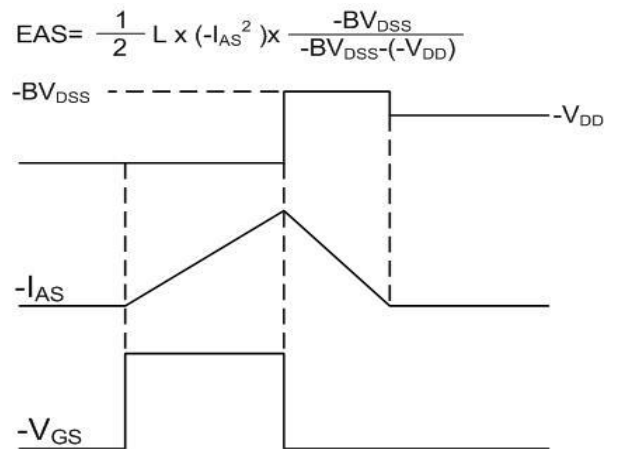


Fig.11 Unclamped Inductive Waveform